

HiPerFET™ Power MOSFETs

ISOPLUS247™

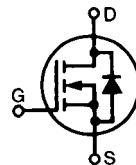
(Electrically Isolated Back Surface)

IXFR 30N50Q
IXFR 32N50Q

V _{DSS}	I _{D25}	R _{DS(on)}
500 V	29 A	0.16 Ω
500 V	30 A	0.15 Ω

t_{rr} ≤ 250 ns

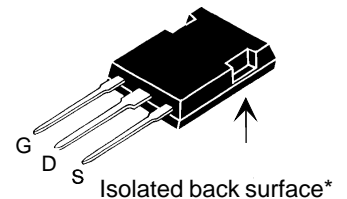
N-Channel Enhancement Mode
High dV/dt, Low t_{rr}, HDMOS™ Family



Preliminary data

Symbol	Test Conditions	Maximum Ratings		
V _{DSS}	T _J = 25°C to 150°C	500	V	
V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	500	V	
V _{GS}	Continuous	±20	V	
V _{GSM}	Transient	±30	V	
I _{D25}	T _C = 25°C	30N50 32N50	30	A
I _{DM}	T _C = 25°C, Pulse width limited by T _{JM}	30N50 32N50	120	A
I _{AR}	T _C = 25°C	30N50 32N50	30	A
E _{AS}	T _C = 25°C	1.5	J	
E _{AR}	T _C = 25°C	45	mJ	
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} T _J ≤ 150°C, R _G = 2 Ω	5	V/ns	
P _D	T _C = 25°C	310	W	
T _J		-55 ... +150	°C	
T _{JM}		150	°C	
T _{stg}		-55 ... +150	°C	
T _L	1.6 mm (0.062 in.) from case for 10 s	300	°C	
V _{ISOL}	50/60 Hz, RMS t = 1 minute leads-to-tab	2500	V~	
Weight		6	g	

ISOPLUS 247™
E 153432



G = Gate D = Drain
S = Source

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
 - High power dissipation
 - Isolated mounting surface
 - 2500V electrical isolation
- Low drain to tab capacitance (<50pF)
- Low R_{DS(on)} HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

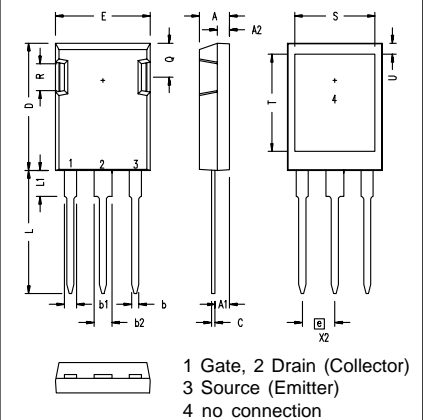
Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _{DSS}	V _{GS} = 0 V, I _D = 1mA	500		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 4mA	2	4	V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0		±100	nA
I _{DSS}	V _{DS} = V _{DSS} V _{GS} = 0 V	T _J = 25°C T _J = 125°C	100 1	μA mA
R _{DS(on)}	V _{GS} = 10 V, I _D = I _T Notes 1, 2	30N50 32N50	0.16 0.15	Ω Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = I_T$ Note 2	18	28	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		3950	pF
C_{oss}			640	pF
C_{rss}			210	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega$ (External),		35	ns
t_r			42	ns
$t_{d(off)}$			75	ns
t_f			20	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$		150	nC
Q_{gs}			26	nC
Q_{gd}			85	nC
R_{thJC}			0.40	K/W
R_{thCK}		0.15		K/W

Source-Drain Diode
Characteristic Values
($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			32 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			128 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = I_S,$ $-di/dt = 100\text{ A/ms},$ $V_R = 100\text{ V}$			250 ns
Q_{RM}			0.75	μC
I_{RM}			7.5	A

- Note: 1. I_T test condition:
IXFR30N50: $I_T = 15\text{ A}$
IXFR32N50: $I_T = 16\text{ A}$
- Note: 2. Pulse test, $t \leq 300\ \mu\text{s}$,
duty cycle $d \leq 2\%$

ISOPLUS 247 (IXFR) OUTLINE


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	13.21	13.72	.520	.540
T	15.75	16.26	.620	.640
U	1.65	3.03	.065	.080

Figure 1. Output Characteristics at 25°C

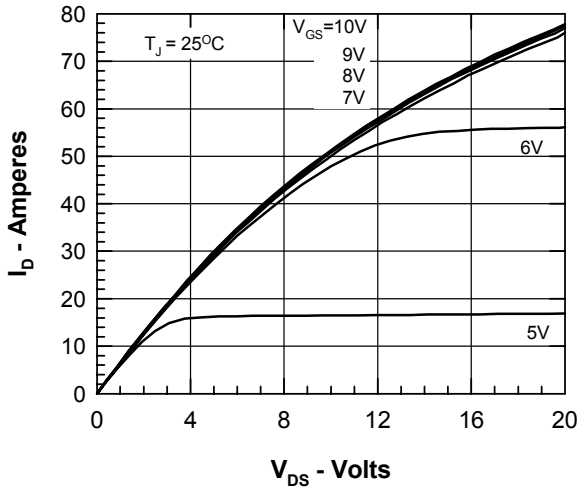


Figure 2. Output Characteristics at 125°C

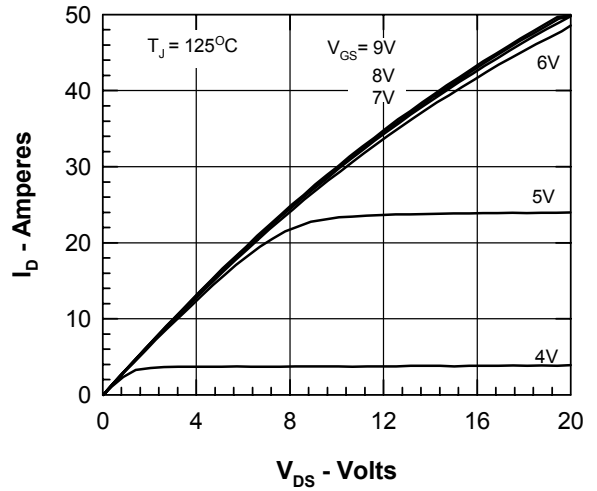


Figure 3. $R_{DS(on)}$ normalized to 15A/25°C vs. I_D

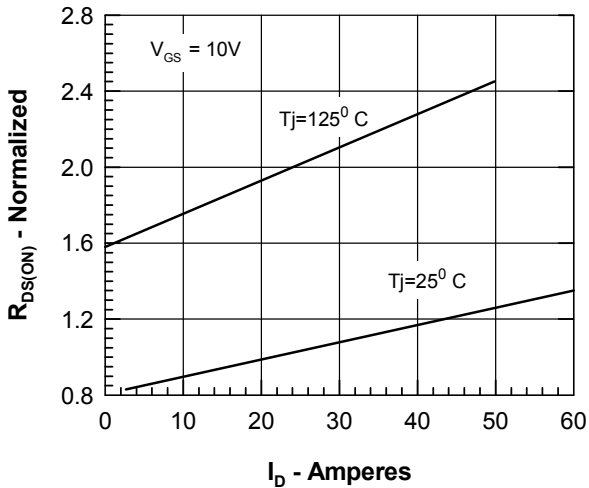


Figure 4. $R_{DS(on)}$ normalized to 15A/25°C vs. T_J

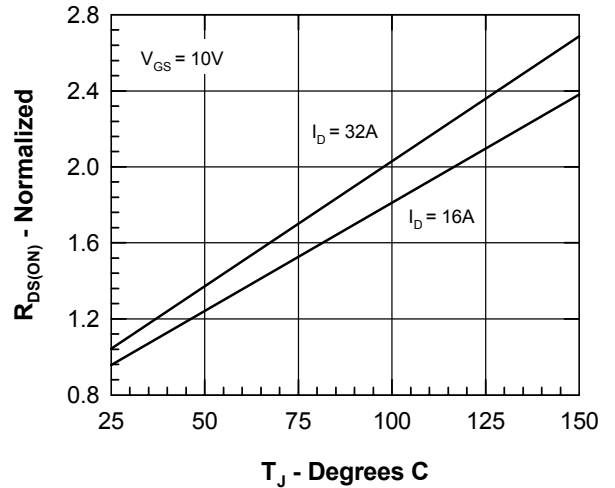


Figure 5. Drain Current vs. Case Temperature

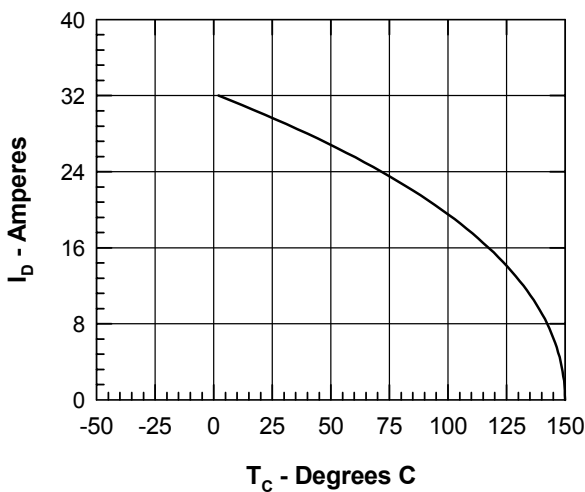


Figure 6. Admittance Curves

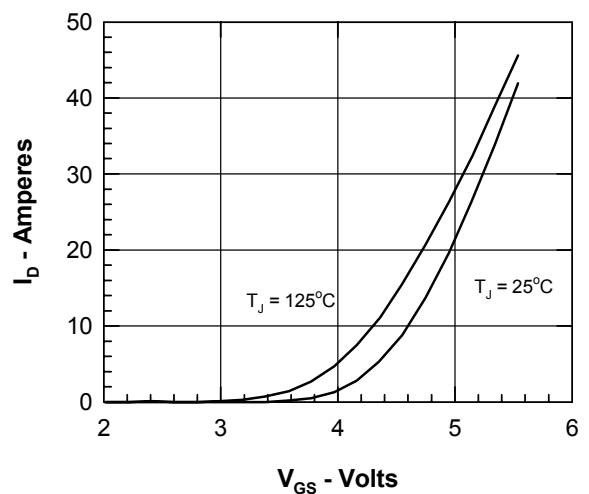


Figure 7. Gate Charge

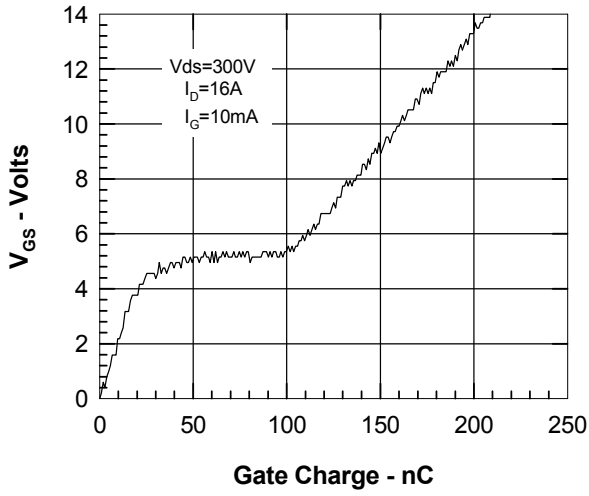


Figure 8. Capacitance Curves

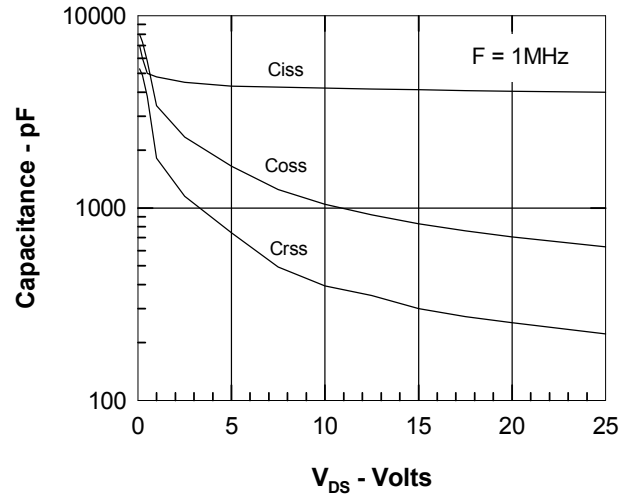


Figure 9. Forward Voltage Drop of the Intrinsic Diode

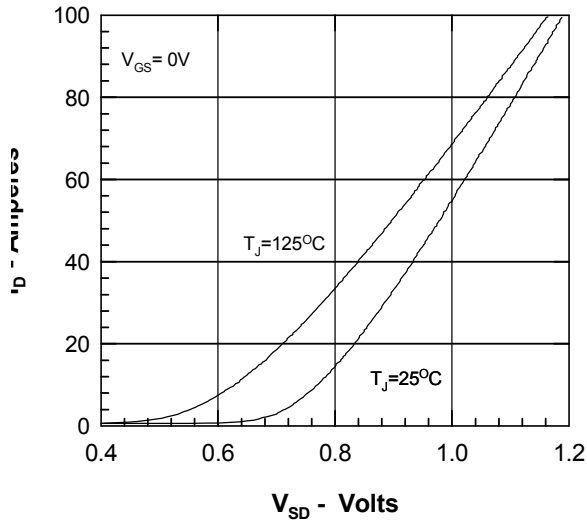


Figure 10. Transient Thermal Resistance

